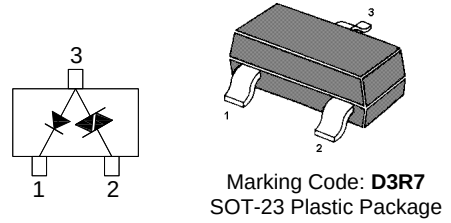


DB307CA

Silicon Rectifier and Trigger Compositod Diodes



Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Non-repetitive Peak Reverse Voltage for Rectifier	V_{RSM}	800	V
Repetitive Peak Reverse Voltage for Rectifier	V_{RRM}	800	V
Non-repetitive Peak Forward Surge Current (8.3 ms) for Rectifier	I_{FSM}	4	A
Repetitive Peak On-state Current ($t_p = 20 \mu\text{s}$, $f = 100 \text{ Hz}$) for Trigger Diodes	I_{TRM}	2	A
Average Rectified Forward Current for Rectifier	$I_{F(AV)}$	200	mA
Operating Junction and Storage Temperature Range	T_j, T_{stg}	- 40 to + 125	$^\circ\text{C}$

Characteristics for Trigger Diodes at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Breakover Voltage at $C = 22 \text{ nF}$	V_{BO}	28	36	V
Dynamic Breakover Voltage at $\Delta I = [I_{BO} \text{ to } I_F = 10 \text{ mA}]$	ΔV	5	-	V
Breakover Current at $C = 22 \text{ nF}$	I_{BO}	-	10	μA
Leakage Current at $V_B = 16 \text{ V}$	I_B	-	1	μA

Characteristics for Rectifier at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage at $I_R = 100 \mu\text{A}$	$V_{(BR)R}$	800	-	V
Forward Voltage at $I_F = 200 \text{ mA}$	V_F	-	1.2	V
Reverse Current at $V_R = 600 \text{ V}$	I_R	-	5	μA

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